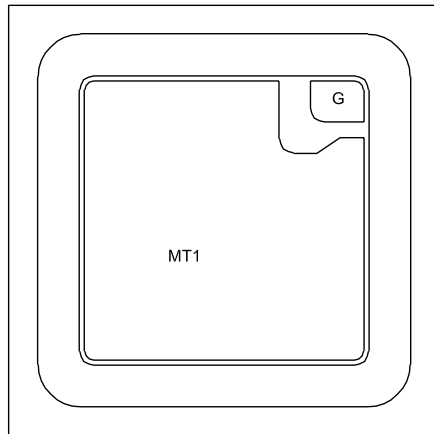


**PROCESS DETAILS**

|                        |                         |
|------------------------|-------------------------|
| Process                | Glass Passivated Mesa   |
| Die Size               | 90 x 90 MILS            |
| Die Thickness          | 8.6 MILS $\pm$ 0.6 MILS |
| MT1 Bonding Pad Area   | 61 x 48 MILS            |
| Gate Bonding Pad Area  | 11 x 9.8 MILS           |
| Top Side Metalization  | Al - 45,000Å            |
| Back Side Metalization | Al/Mo/Ni/Ag - 32,000Å   |

**GEOMETRY**

R0

**BACKSIDE MT2****GROSS DIE PER 4 INCH WAFER**

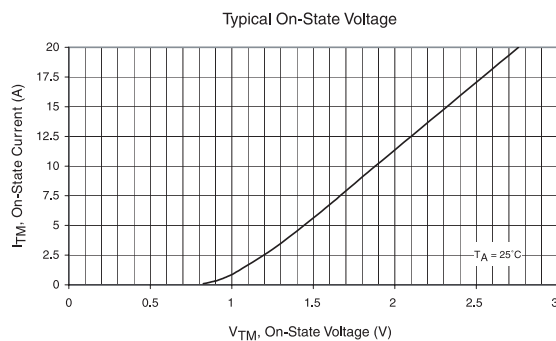
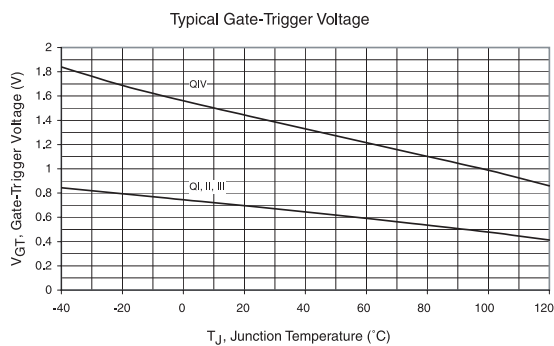
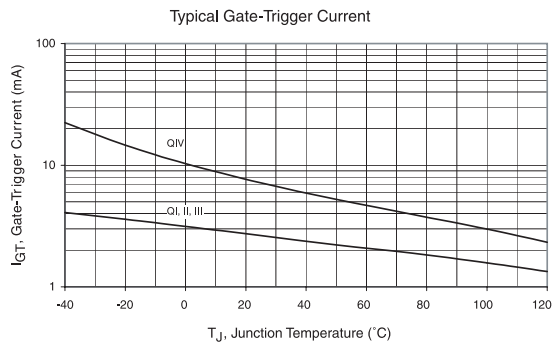
1,310

**PRINCIPAL DEVICE TYPES**

2N6075A  
CQ202-4MS  
CQ223-4M  
CQD-4M

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centralsemi.com](http://www.centralsemi.com)

R1 (19 -May 2005)



145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centralsemi.com](http://www.centralsemi.com)

R1 (19 -May 2005)